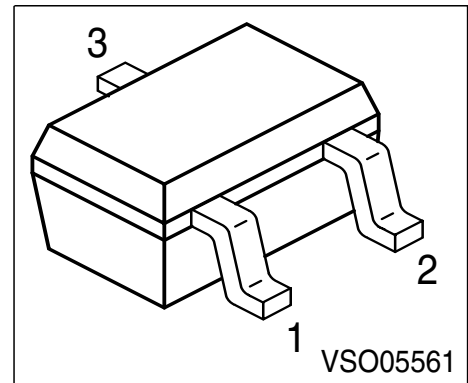


NPN Silicon RF Transistor

- Especially suitable for TV-sat and UHF tuners



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BF 775W	LOs	1 = B	2 = E	3 = C	SOT-323

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	15	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2.5	
Collector current	I_C	30	mA
Base current	I_B	4	
Total power dissipation, $T_S \leq 86^\circ\text{C}$ (F)	P_{tot}	280	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point	R_{thJS}	≤ 230	K/W
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¹ T_S is measured on the collector lead at the soldering point to the pcb

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 2.5 \text{ V}, I_C = 0$	I_{EBO}	-	-	100	μA
DC current gain $I_C = 15 \text{ mA}, V_{CE} = 8 \text{ V}$	h_{FE}	40	100	200	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC characteristics (verified by random sampling)					
Transition frequency $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	3.5	5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	0.43	0.6	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ce}	-	0.25	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	0.7	-	
Noise figure $I_C = 2\text{ mA}$, $V_{CE} = 6\text{ V}$, $Z_S = Z_{\text{Sopt}}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	F	-	1.8	-	dB
		-	2.9	-	
Power gain, maximum available ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{\text{Sopt}}$, $Z_L = Z_{\text{Lopt}}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	G_{ma}	-	15.5	-	
		-	10	-	
Transducer gain $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	13	-	
		-	7.5	-	

$$^1G_{\text{ma}} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

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